

L810N-40M32L Higher Beam Type LED

L810N-40M32L is an AlGaAs LED mounted on a TO-18 stem with glass ball lens. It is designed for high beam use. On forward bias, it emits a spectral band of radiation which peaks at 810nm.

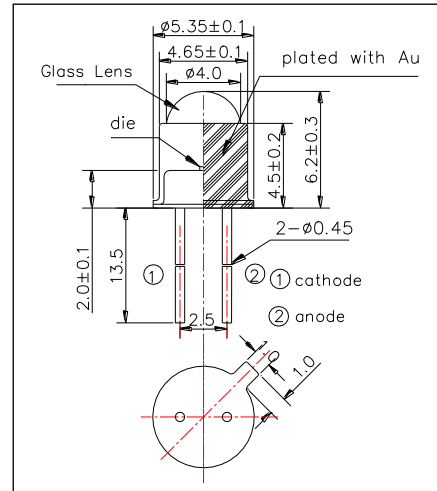
<Features>

- High Radiated Intensity
- High Reliability

<Specifications>

1. Product Name: Infrared LED Lamp
2. Type Number: L810N-40M32L
3. Chip:
 - Chip material: AlGaAs
 - Peak Wavelength: 810nm
4. Package
 - Type: TO-18 Stem
 - Lens: Glass Ball Lens
 - Cap: Gold Plated

Outer Dimension (Unit:mm)



Absolute Maximum Ratings				
Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	PD	190	mW	Ta=25°C
Forward Current	IF	100	mA	Ta=25°C
Pulse Forward Current*	IFP	1000	mA	Ta=25°C
Reverse Voltage	VR	5	V	Ta=25°C
Operating Temperature	TOPR	-30 ~ +80	°C	
Storage Temperature	TSTG	-30 ~ +100	°C	
Soldering Temperature**	TSOL	265	°C	

* Duty=1% and Pulse Width=10μs.

** Soldering condition must be completed within 3 second at 265 °C.

Electro-Optical Characteristics						
Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	IF=50mA		1.55	1.65	V
Reverse Current	IR	VR=5V			10	uA
Total Radiated Power*	PO	IF=50mA	8	12		mW
Radiant Intensity**	IE	IF=50mA		100		mW/sr
Peak Wavelength	λP	IF=50mA	800	810	820	nm
Half Width	Δλ	IF=50mA		40		nm
Viewing Half Angle	θ1/2	IF=50mA		±8.5		deg
Rise Time	tr	IF=50mA		25		ns
Fall Time	tf	IF=50mA		20		ns

* Measured by Photodyne #500

** Measured by Tektronix J-6512

